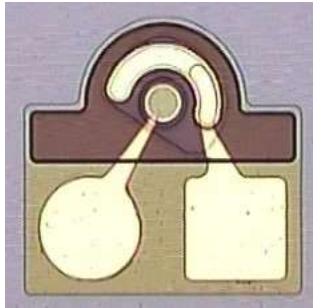


25Gbps InGaAs PD

PD1316G025

Preliminary



Feature

- 25um optical detection mesa area.
- Top-side illuminated device.
- AR coating for wide wavelength range.
- High cut-off frequency.
- Low dark current and capacitance..

Device Electro-Optical Characteristics

All parameters for T = 25°C unless otherwise noted.

PARAMETER	SYMBOL	UNIT	MIN.	TYP.	MAX.	TEST CONDITIONS
Breakdown Voltage	Vbr	V	20			Id=-10uA
Dark Current	Id	nA		1	50	V=-5V
Capacitance	C	pF		0.08	0.15	V=-5V, f=1MHz
Responsivity	R	A/W		0.75		λ=1310nm
Overload	Po	dBm	0			λ=1310nm
Bandwidth	3dB	GHz		20		V=-5V

Device Physical Specifications

PARAMETER	UNIT	MIN.	TYP.	MAX.
Bond Pad	um		ψ70	
Device Size	um		250X250	
Device Hight	um		150	

Device Physical Specifications 1X4 array

PARAMETER	UNIT	MIN.	TYP.	MAX.
Bond Pad	um		ψ70	
Chip size	um		250X1000	
Chip Hight	um		150	

Absolute Maximum Ratings

PARAMETER	SYMBOL	UNIT	Ratings
Forward Current	I _f	mA	5
Reverse Voltage	V _r	V	20
Operating Temperature	T _o	°C	-40 to +90
Storage Temperature	T _{st}	°C	-40 to +100
Incident Optical power	P _m	dBm	+3dBm

Order Information

PD1316G025-A01: 25 Gbps InGaAs PD Single Chip

PD1316G025-A04: 25 Gbps InGaAs PD 1X4 array